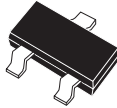


CMPT8099 NPN
CMPT8599 PNP

COMPLEMENTARY
SILICON TRANSISTOR



SOT-23 CASE

CentralTM
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMPT8099, CMPT8599 types are Complementary Silicon Transistors manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for general purpose audio amplifier applications.

Marking Codes are CKB and C2W Respectively.

MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$)

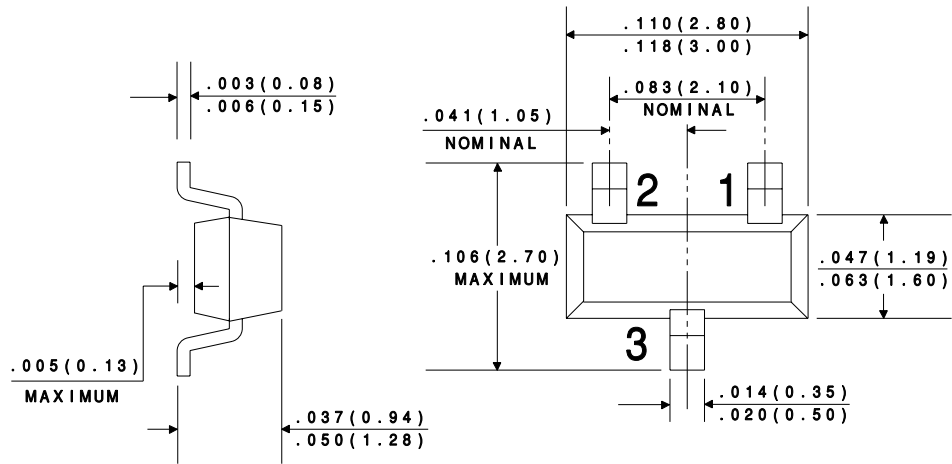
	SYMBOL	CMPT8099	CMPT8599	UNITS
Collector-Base Voltage	V_{CB0}	80	80	V
Collector-Emitter Voltage	V_{CEO}	80	80	V
Emitter-Base Voltage	V_{EBO}	6.0	5.0	V
Collector Current	I_C	500		mA
Power Dissipation	P_D	350		mW
Operating and Storage				
Junction Temperature	T_J, T_{stg}	-65 to +150		$^{\circ}\text{C}$
Thermal Resistance	Q_{JA}	357		$^{\circ}\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	CMPT8099		CMPT8599		UNITS
		MIN	MAX	MIN	MAX	
I_{CBO}	$V_{CB}=80\text{V}$		0.1		0.1	mA
I_{EBO}	$V_{BE}=6.0\text{V}$		0.1		-	mA
I_{EBO}	$V_{BE}=4.0\text{V}$		-		0.1	mA
BV_{CBO}	$I_C=100\text{mA}$	80		80		V
BV_{CEO}	$I_C=10\text{mA}$	80		80		V
BV_{EBO}	$I_E=10\text{mA}$	6.0		5.0		V
$V_{CE(SAT)}$	$I_C=100\text{mA}, I_B=5.0\text{mA}$		0.4		0.4	V
$V_{CE(SAT)}$	$I_C=100\text{mA}, I_B=10\text{mA}$		0.3		0.3	V
$V_{BE(ON)}$	$V_{CE}=5.0\text{V}, I_C=10\text{mA}$	0.6	0.8	0.6	0.8	V
h_{FE}	$V_{CE}=5.0\text{V}, I_C=1.0\text{mA}$	100	300	100	300	
h_{FE}	$V_{CE}=5.0\text{V}, I_C=10\text{mA}$	100		100		

SYMBOL	TEST CONDITIONS	CMPT8099		CMPT8599		UNITS
		MIN	MAX	MIN	MAX	
h_{FE}	$V_{CE}=5.0V, I_C=100mA$	75		75		
f_T	$V_{CE}=5.0V, I_C=10mA, f=100MHz$	150		150		MHz
C_{ob}	$V_{CB}=10V, I_E=0, f=1.0MHz$		6.0		4.5	pF
C_{ib}	$V_{BE}=0.5V, I_C=0, f=1.0MHz$		25		30	pF

All dimensions in inches (mm).



LEAD CODE:

- 1) BASE
- 2) EMITTER
- 3) COLLECTOR